Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	110	(((thin near2 film) tft transistor) near2 array) and gate and data and insulat$4 and ("a-si:C:O" "a-si:O:F") and pixel and electrode and dielectric and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:23
L2	61	1 not samsung.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:22
L3	1	((((thin near2 film) tft transistor) near2 array) and gate and data and insulat$4 and ("a-si:C:O" "a-si:O:F") and pixel and electrode and dielectric and hole).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:25
L4	279	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:23
L6	1579	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:23
L7	1860	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:23
L8	339	257/225	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 09:25
S1	34614	"349"/$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/24 08:42
S2	1645	((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat$4 and dielectric and (pixel near4 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 08:53

S3	811	"349"/$6 and (((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat$4 and dielectric and (pixel near4 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/24 08:45
S4	113819	silicon near3 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:22
S5	1380	((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or data or signaling) near3 (line or electrode)) and array and insulat$4 and dielectric and (pixel near4 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/24 08:46
S6	1708	((thin near3 film near3 transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat$4 and dielectric and (pixel near4 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:20
S7	1728	((thin near3 film near3 transistor) or (tft)) and substrate and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and dielectric and (pixel near4 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:20
S8	576	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and dielectric and (pixel near4 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:21
S9	418	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:01
S10	118878	silicon near3 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:23

S11	295	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:23
S12	241750	(indium near3 (tin or zinc) near3 oxide) or ito or izo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:24
S13	236208	(indium adj (tin or zinc) adj oxide) or ito or izo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:24
S14	277	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and ((indium adj (tin or zinc) adj oxide) or ito or izo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:24
S15	4402	((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:25
S16	203	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 09:25
S17	790203	chrom$4 or cr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:11
S18	4230267	aluminum or al	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:12

S19	150	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and (chrom$4 or cr) and (aluminum or al)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:45
S20	448074	molybdenum or mo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:46
S21	96476	(chrom$4 or cr) and (aluminum or al) and (molybdenum or mo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:47
S22	243803	((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:49
S23	87	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data) near3 (line or electrode)) and array and insulat$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom$4 or cr) and (aluminum or al) and (molybdenum or mo)) and (((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 10:53
S24	67	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:13

S25	54	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:02
S26	51	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and ((indium adj (tin or zinc) adj oxide) or ito or izo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:02
S27	34	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:04
S28	33	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:05
S29	1426	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:10
S30	2218	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:05

S31	3078	349/43 or 349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:06
S32	11	((((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (349/43 or 349/42)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:10
S33	358	349/51	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:10
S34	89	349/52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:10
S35	3427	349/43 or 349/42 or 349/51 or 349/52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:11
S36	11	((((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan$4 or data or drain or source) near3 (line or electrode)) and array and insulat$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (349/43 or 349/42 or 349/51 or 349/52)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:11
S37	6754	insulat$4 near8 (dielectric and silicon near3 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:12

S38	90796	(gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:14
S39	42185	((thin near3 film near3 transistor) or (tft)) and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:14
S40	706656	(drain or data or source or signal$4) near3 (line or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:15
S41	718	(insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:15
S42	32786	passivation near3 (film or layer or plate or coat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:16
S43	290	((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:29
S44	1799	(passivation near3 (film or layer or plate or coat$4)) same ((chemical near3 vapor near3 deposit$3) or pevcd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:31
S45	21	((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and ((passivation near3 (film or layer or plate or coat$4)) same ((chemical near3 vapor near3 deposit$3) or pevcd))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:17

S46	152	"349"/$6 and (((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:18
S47	6	"349"/$6 and (((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and ((passivation near3 (film or layer or plate or coat$4)) same ((chemical near3 vapor near3 deposit$3) or pevcd)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:18
S48	138	(((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4))) and ((dielectric or permittiv$4) near3 (constant or coefficient))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:30
S49	74	((((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4))) and ((dielectric or permittiv$4) near3 (constant or coefficient))) and "349"/$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/09 11:30

S50	32	(((((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4))) and ((dielectric or permittiv$4) near3 (constant or coefficient))) and "349"/$6) and ((chemical near3 vapor near3 deposit$3) or pevcd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 10:57
S51	13656	second near3 ((gate or scan$4) and insulat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 11:19
S52	16	(((((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4))) and ((dielectric or permittiv$4) near3 (constant or coefficient))) and "349"/$6) and (second near3 ((gate or scan$4) and insulat$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 11:20
S53	7610	(second near3 insulat$4) same (nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 11:20
S54	8	(((((insulat$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan$4) near8 ((chrom$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat$4))) and ((dielectric or permittiv$4) near3 (constant or coefficient))) and "349"/$6) and ((second near3 insulat$4) same (nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 11:21

S55	12	"a-si:c:o" or "a-si:o:f"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 11:26
S56	3	("a-si:c:o" or "a-si:o:f") and "349"/$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/10 11:26
S57	302	tao$2 near8 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 14:06
S58	12	(tao$2 near8 dielectric) and "349"/$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 14:06
S59	1948	((first or lower) near3 (gate or scan$4) near3 (insulat$5)) near9 (sio or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 14:41
S60	1976	((first or lower) near3 (gate or scan$4) near3 (insulat$5)) near9 (sio$4 or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 14:42
S61	129	(((first or lower) near3 (gate or scan$4) near3 (insulat$5)) near9 (sio$4 or silicon)) and "349"/$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/27 14:42
S62	129	"a-si:o:f" "a-si:c:o"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 14:48
S63	123	S62 and ((liquid near2 crystal) lcd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 14:49
S64	123	S62 and ((liquid near2 crystal) lcd)S63 and substrate and gate and tft and (pixel near2 elecrtode) and insulat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 14:53

S65	66	S64 not samsung.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 14:54